Possibly relevant new from RD50

G. Casse

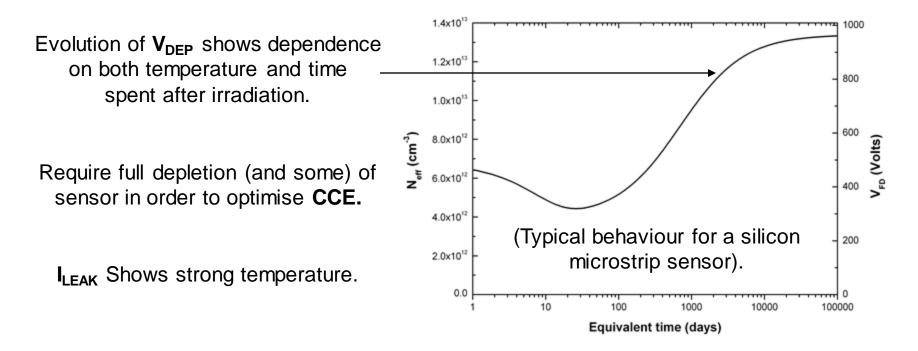


23th November 2010

Annealing: p-in-n, n-in-p (n) Charge trapping Multiplication

Evolution of Sensor Properties After Irradiation

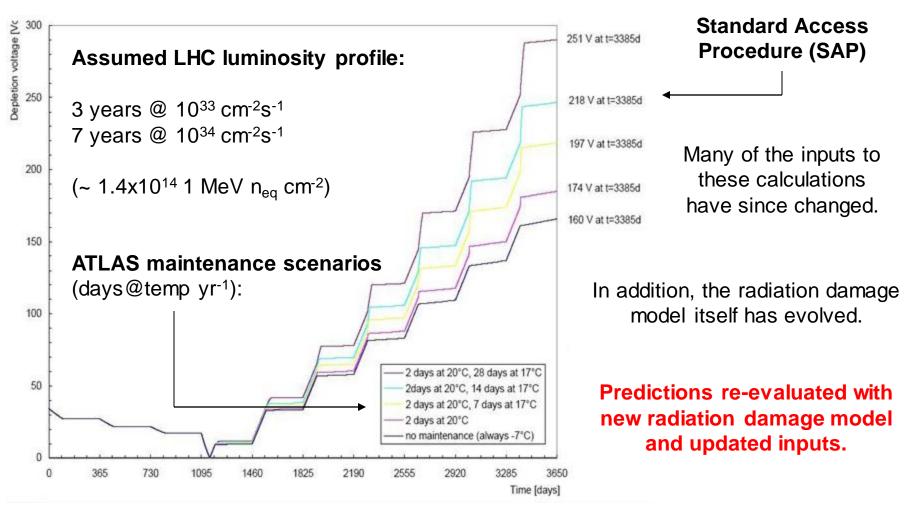
Sensor leakage current (I_{LEAK}), depletion voltage (V_{DEP}) and charge collection efficiency (CCE) are all affected by irradiation.



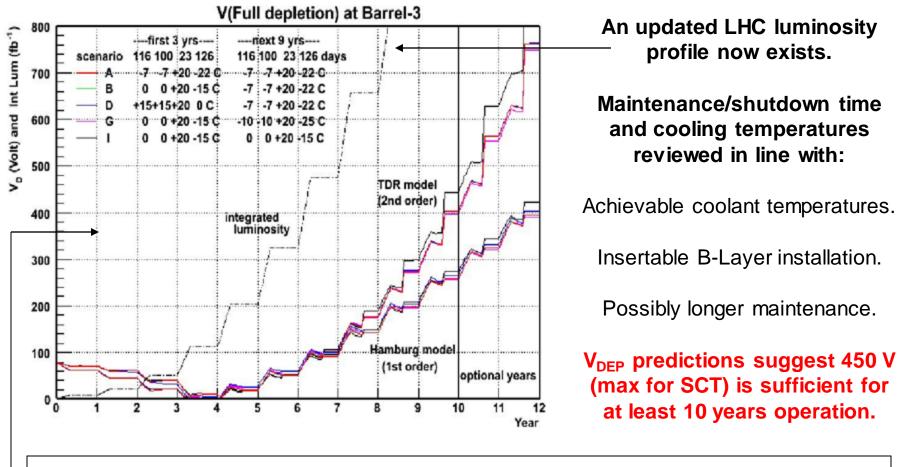
Need to avoid the sensors being warm (> 0 °C) for long periods of time!

Evaluating the Evolution of V_{DEP} and I_{LEAK} in the SCT

In the ATLAS Inner Detector Technical Design Report (1997) V_{DEP} and I_{LEAK} were predicted for SCT sensors.



Re-Evaluating the Evolution of V_{DEP} and I_{LEAK} in the SCT



Paul Dervan, Joost Vossebeld, Tim Jones (Liverpool), Taka Kondo (KEK), Graham Beck (QMUL), Georg Viehhauser (Oxford), Steve McMahon (RAL), Koichi Nagai (Brookhaven), Kirill Egorov (Indiana), Richard Bates, Alexander Bitadze (Glasgow).

Comparison of Hamburg Model and TDR Model

Hamburg model is now believed to be the best model available to predict V_{DEP}.

However, large differences observed between the predictions of the TDR model and the Hamburg model.

Origin is in **reverse annealing** contribution ΔN_Y to the predicted change in effective doping concentration ΔN_{EFF} :

$$\Delta N_{EFF}(\Phi,T,t) = \Delta N_{C}(\Phi) + \Delta N_{A}(\Phi,T,t) + \Delta N_{Y}(\Phi,T,t) \qquad V_{DEP} = \frac{ed^{2}|N_{EFF}|}{2\varepsilon}$$

TDR model parameterised reverse annealing as a **second order process**.

Hamburg model parameterises reverse annealing as a modified first order process.

Need high fluence + long annealing data to compare to predictions of both models.

Programme of Accelerated Annealing Measurements

Sensor performance traditionally studied by determining V_{DEP} from CV measurements.

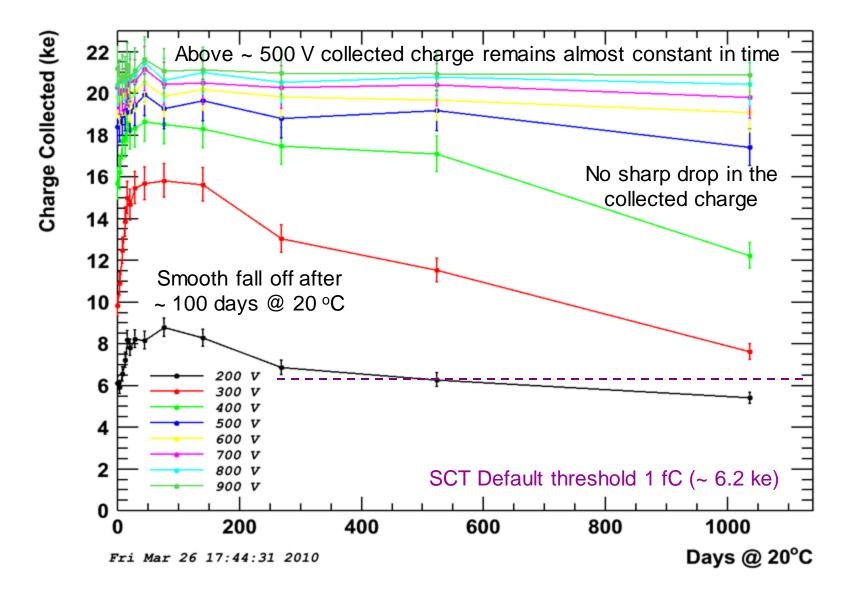
In **Liverpool** the focus has been on **measuring the annealing of CCE**. Much data available for n-side readout sensors. Less detailed information for p-in-n sensors.

New programme of accelerated annealing	Manufacturer	HPK
measurements on ATLAS mini sensors.	Wafer Tech.	FZ
Pair of sensors irradiated with neutrons at Ljublijana (V. Cindro et al) to 2x10¹⁴ 1 MeV n_{eq} cm⁻²	Structure	p-in-n
	Size	1 cm x 1 cm
(new prediction for SCT = 1.6×10^{14} 1 MeV n_{eq} cm ⁻²).	Thickness	285 µm

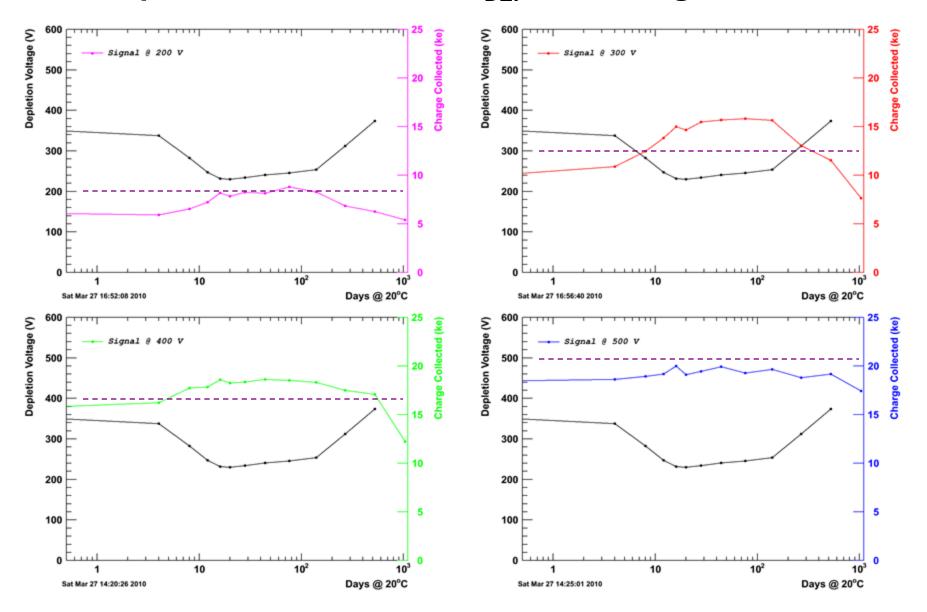
One sensor used for CCE measurements and one sensor used for V_{DEP} measurements. Both **sensors annealed together** at same temperature for same length of time.

> All following plots by.... A. Affolder, H. Brown, G. Casse, P. Dervan, J. Vossebeld, C. Wiglesworth (Liverpool)

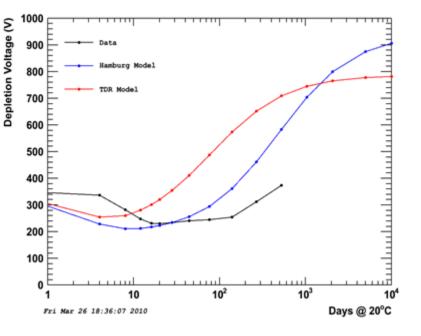
Results of Charge Collection Measurements



Comparison of Measured V_{DEP} and Charge Collected

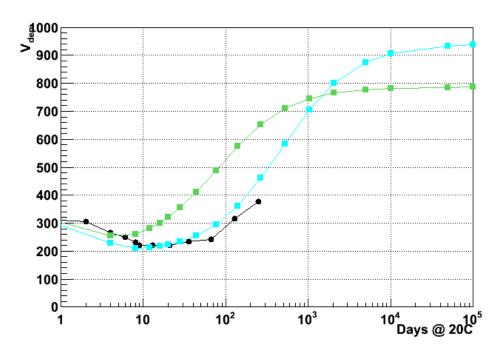


Comparison of Predicted V_{DEP} and Measured V_{DEP}

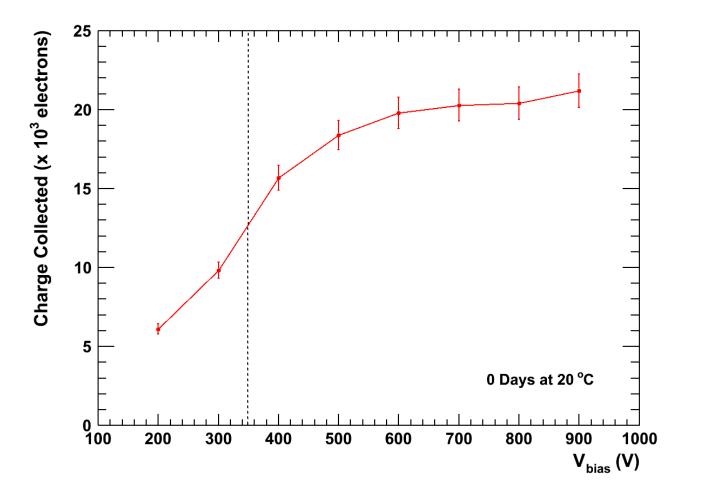


Data shows a slower annealing effect than the two models

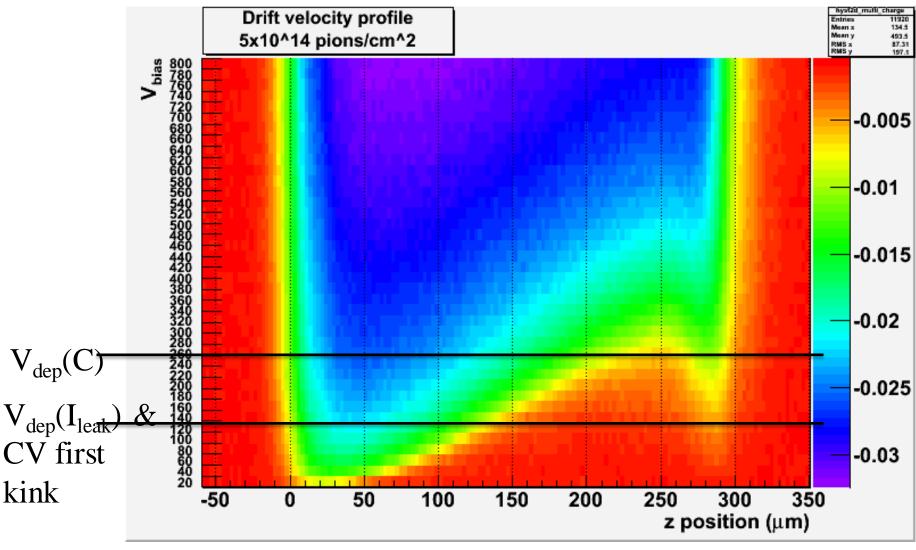
Data looks closer to Hamburg model



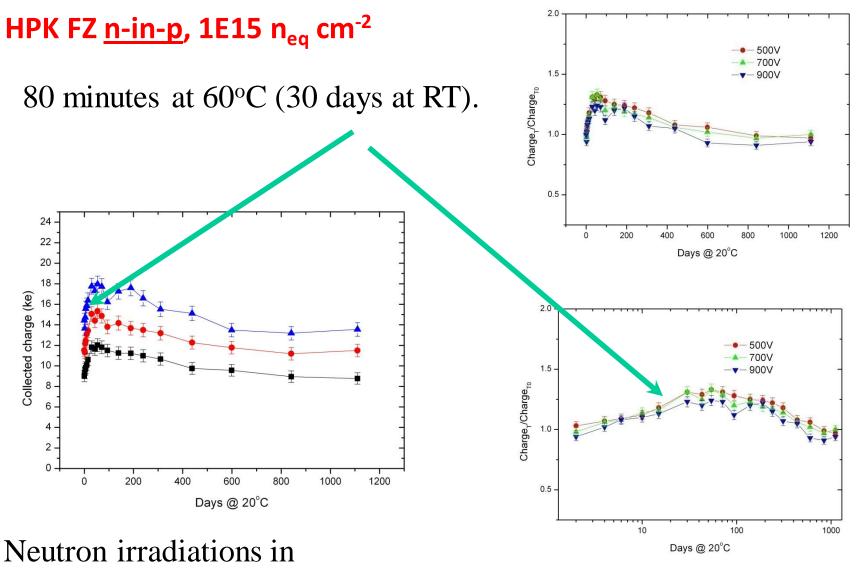
A warning about Comparing V_{DEP} (CV) to signal collected



Drift velocity profile: $5x10^{14} \pi/cm^2$ irradiated detector



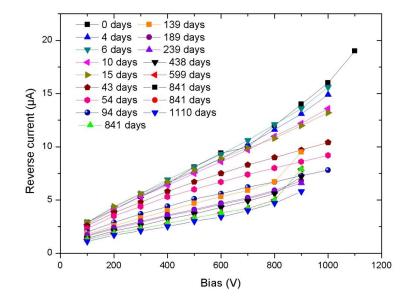
Using fixed annealing time for comparison of the electrical properties

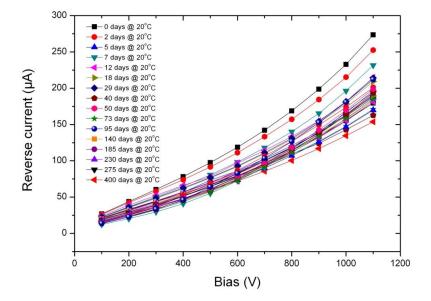


Ljubljana.

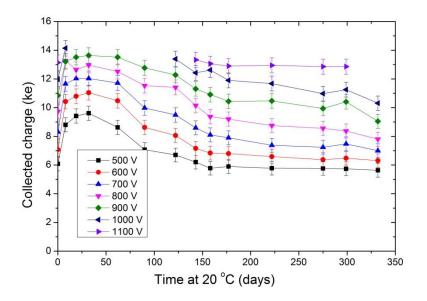
G. Casse, 19th RD50, CERN 21-23 Nov. 2011

Accelerated Annealing of the reverse current, n-in-p sensors, 1E15 and 1.5E16 n cm⁻²

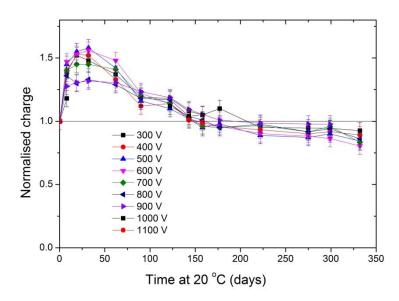




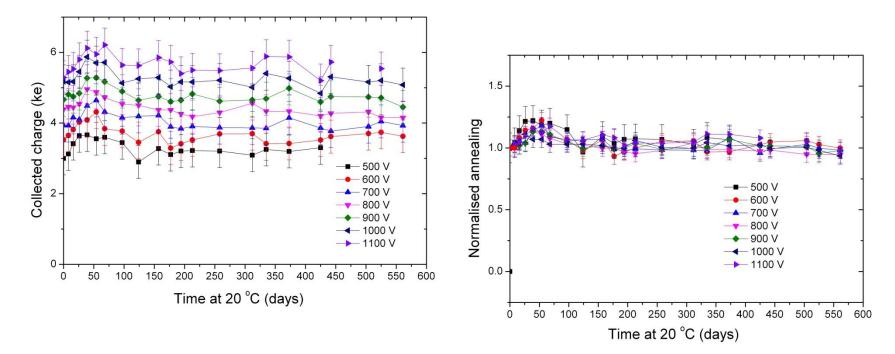
Room Temperature Annealing of the collected charge, HPK FZ n-in-p, 2E15 n cm⁻² (26MeV p irradiation)



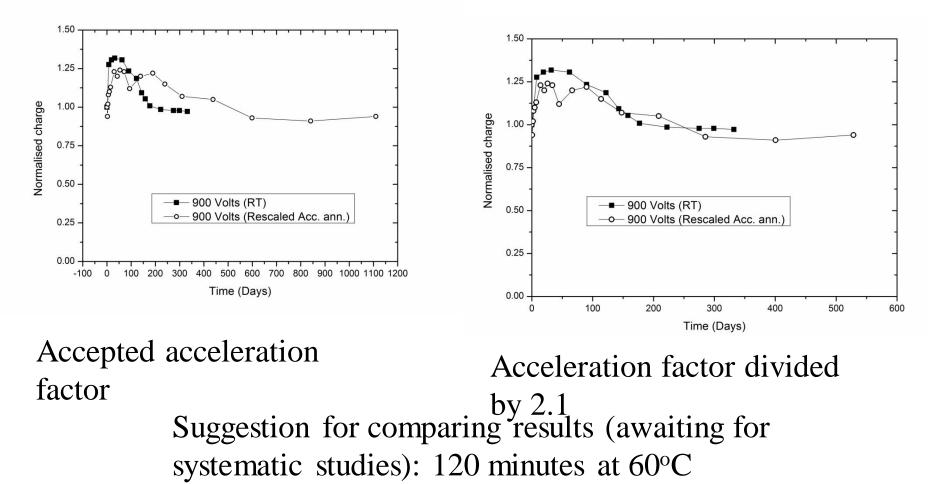
We make large use of accelerating annealing: is this a safe and correct approach?



Room Temperature Annealing of the collected charge, HPK FZ n-in-p, 1E16 n cm⁻² (26MeV p irradiation)

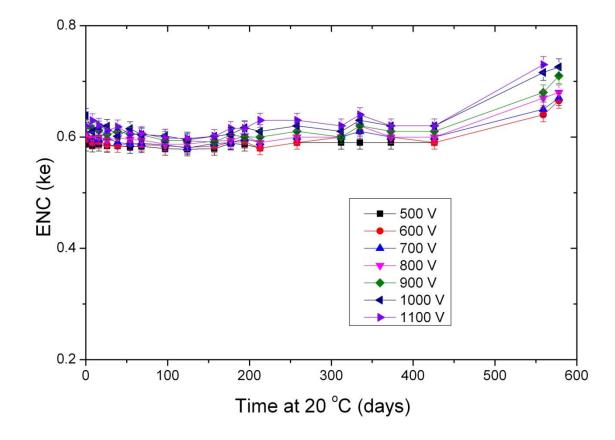


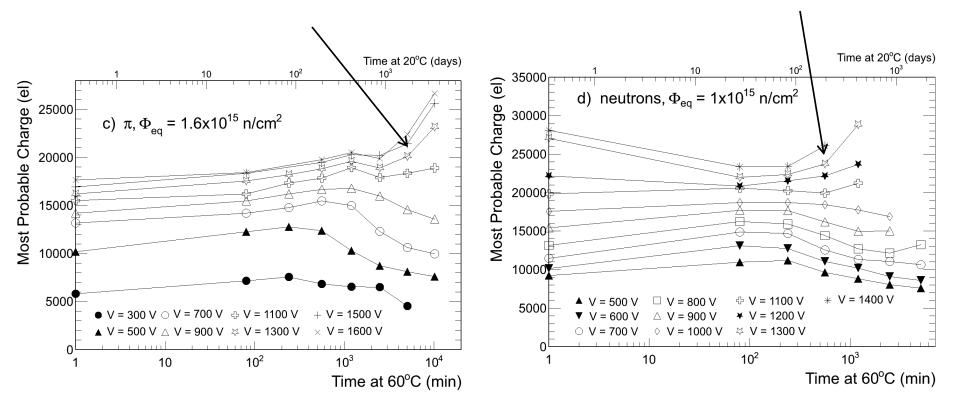
Comparison of Room Temperature and Accelerated Annealing of the collected charge, HPK FZ n-in-p, 1and 1.5E15 n cm⁻² (26MeV p irradiation)



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Noise

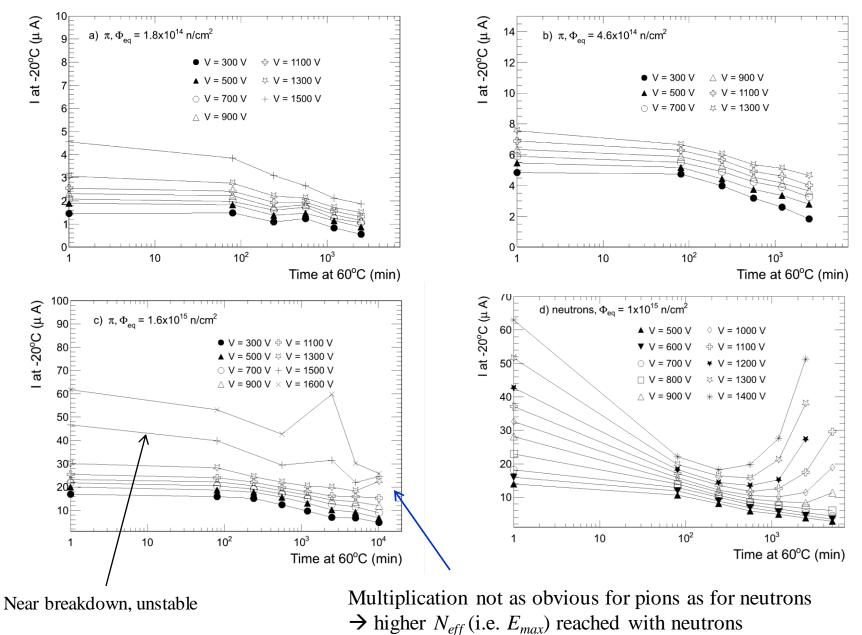




- multiplication obvious in detectors irradiated with pions after longer annealing times then after irradiation with neutrons:
 - → smaller introduction rates for pions → takes longer to reach sufficient N_{eff} for high enough peak electric field

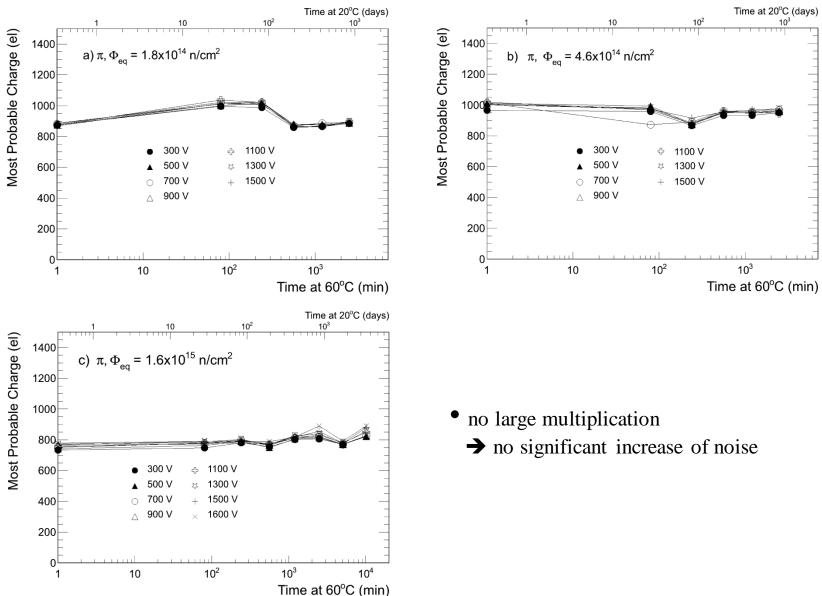
 $\rightarrow N_{eff} \sim 4e13 \text{ cm}^{-3}$ at annealing points where multiplication starts to be obvious

Detector current



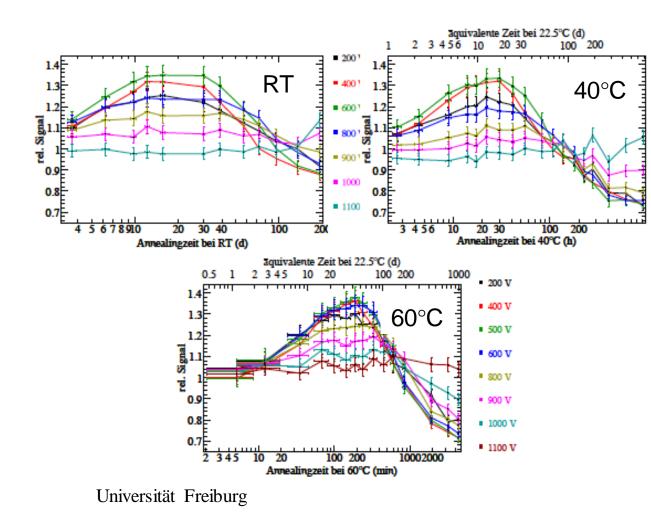
I. Mandić, 19th RD50 Workshop, CERN, 21 – 23 November 2011

<u>Noise</u>



Relative signal

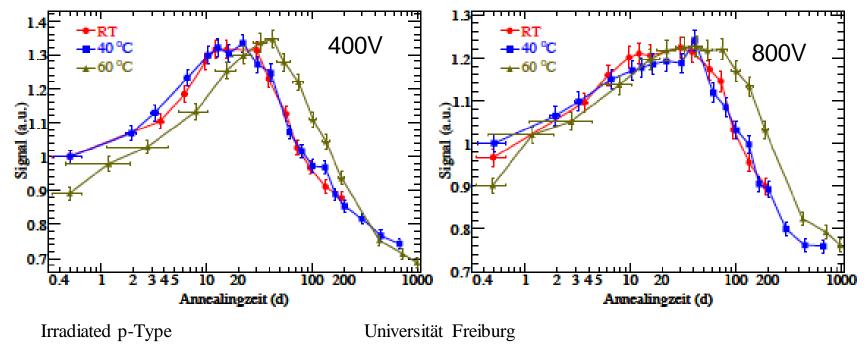
- Signal normalised to pre-annealing signal
 - N.B.: different time ranges in plots
- Beneficial and reverse annealing visible
- Higher bias voltages are less affected by annealing



Annealing Studies of Irradiated p-Type

Scaling

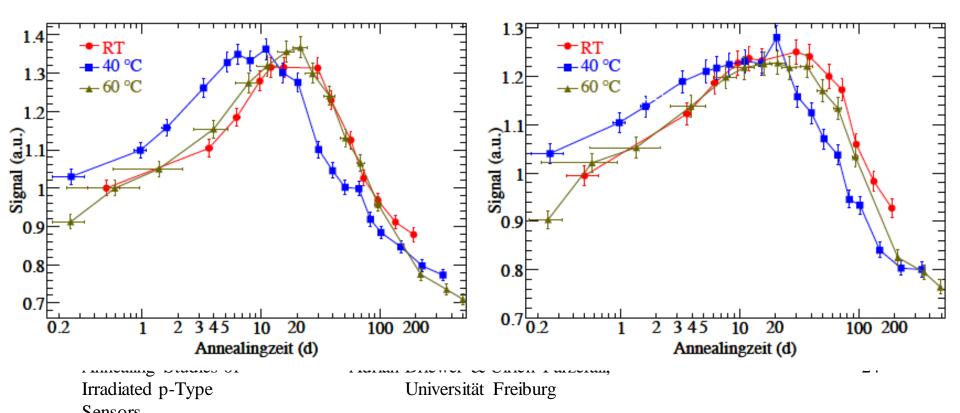
- Comparison of signal evolution for RT, 40° , 60°
- RD48 Model does not scale 60° data correctly to RT
- Annealing at 60° appears "too slow"
- As observed by e.g. Gianluigi: scale factor appears too large



Soncore

Scaling

- Signal comparison for RT, 40° , 60°
- As before, but scale factor reduced by ~2
- Reasonable agreement between RT and 60° CCE data (as previously reported by G.C.)



Time Evolution

- Repeated measurement of signal spectra
 - Same sensor, same conditions, 7 days later
- Landau signal peak narrows with time (sensor stored cold)

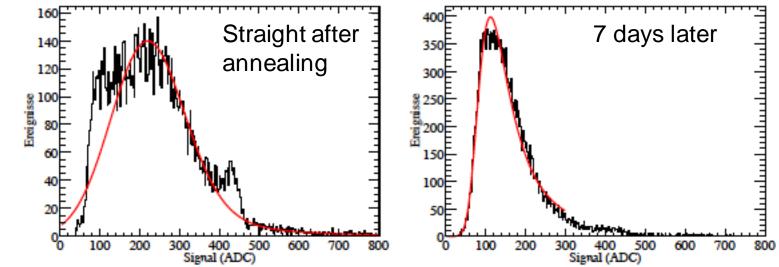


Abbildung 7.9: Signalspektrum von Messungen direkt nach der Wärmebehandlung (links) und 7 Tage später (rechts). Irradiated p-Type Universität Freiburg

Charge trapping parameters

Was not parameterised at the TDR times.

G. Kramberger et al., NIMA, Volume 579, Issue 2, 1 September 2007, Pages 762-765

$$1/\tau_{effe,h} = \beta_{e,h}(t,T)\Phi_{eq}$$

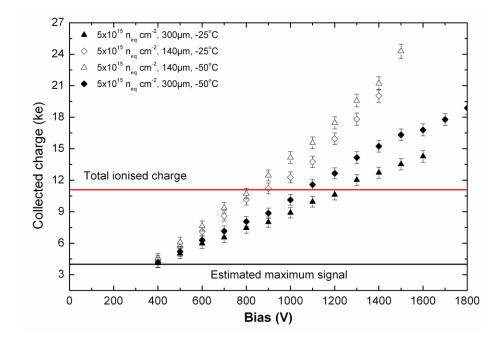
Reactor neutrons	5.7±1	3.7 ± 0.6
Fast charged	6.6±0.9	5.4 ± 0.4
hadrons		

$$\beta_{\mathrm{e},\mathrm{h}}(t) = \beta_{\mathrm{0e},\mathrm{h}} \cdot \mathrm{e}^{-t/\tau}_{\mathrm{e},\mathrm{h}} + \beta_{\mathrm{\infty e},\mathrm{h}} \cdot (1 - \mathrm{e}^{-t/\tau}_{\mathrm{e},\mathrm{h}})$$

	au (min at)	$(eta_0 - eta_\infty)/eta_0$	$E_{ta} (\mathrm{eV})$
Electrons	650±250	0.35 ± 0.15	1.06 ± 0.1
Holes	530±250	-0.4 ± 0.2	0.98 ± 0.1

140 and 300 μm n-in-p Micron sensors after $5x10^{15}$ n_{eq} 26MeV p

Evidence of a charge multiplication effect: not only the whole charge is recovered, but increased by f = 1.75



G. Casse, Prague, June 2010